



# PH16030L

## N-channel TrenchMOS™ logic level FET

Rev. 01 — 24 February 2005

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS™ technology.

### 1.2 Features

- Logic level threshold
- SO8 equivalent area footprint
- Low thermal resistance
- Low gate charge.

### 1.3 Applications

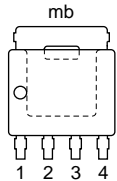
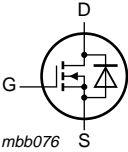
- DC-to-DC converters
- Portable appliances.

### 1.4 Quick reference data

- $V_{DS} \leq 30$  V
- $R_{DS(on)} \leq 16.9$  m $\Omega$
- $I_D \leq 38$  A
- $Q_{gd} = 2.9$  nC (typ).

## 2. Pinning information

Table 1: Pinning

Pin	Description	Simplified outline	Symbol
1, 2, 3	source		
4	gate		
mb	mounting base; connected to drain		

SOT669 (LFPAK)

# PHILIPS

### 3. Ordering information

**Table 2: Ordering information**

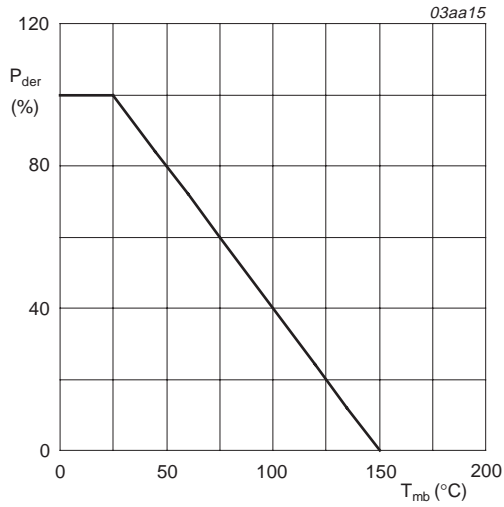
Type number	Package		Version
	Name	Description	
PH16030L	LFAK	plastic single-ended surface mounted package; 4 leads	SOT669

### 4. Limiting values

**Table 3: Limiting values**

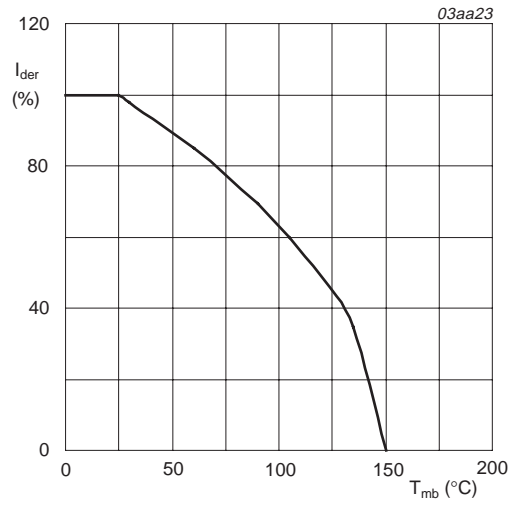
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	30	V
$V_{DGR}$	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	gate-source voltage (DC)		-	$\pm 15$	V
$I_D$	drain current (DC)	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Figure 2</a> and <a href="#">3</a>	-	38	A
		$T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Figure 2</a>	-	24	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Figure 3</a>	-	100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Figure 1</a>	-	41.6	W
$T_{stg}$	storage temperature		-55	+150	°C
$T_j$	junction temperature		-55	+150	°C
<b>Source-drain diode</b>					
$I_S$	source (diode forward) current (DC)	$T_{mb} = 25\text{ °C}$	-	38	A
$I_{SM}$	peak source (diode forward) current	$T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	100	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 21\text{ A}$ ; $t_p = 0.1\text{ ms}$ ; $V_{DD} \leq 25\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; starting at $T_j = 25\text{ °C}$	-	44	mJ



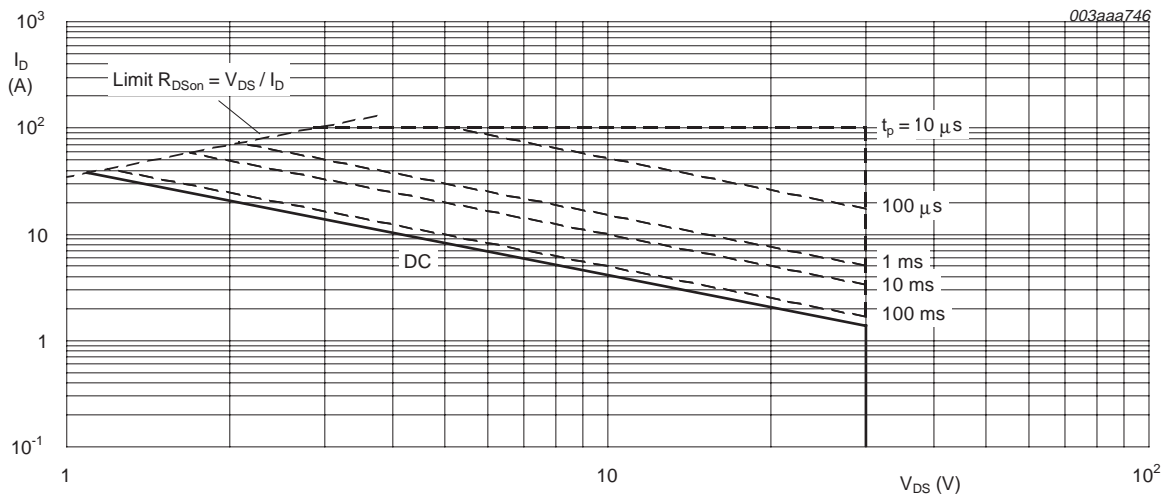
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature



$T_{mb} = 25^{\circ}\text{C}$ ;  $I_{DM}$  is single pulse;  $V_{GS} = 10\text{ V}$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	3	K/W

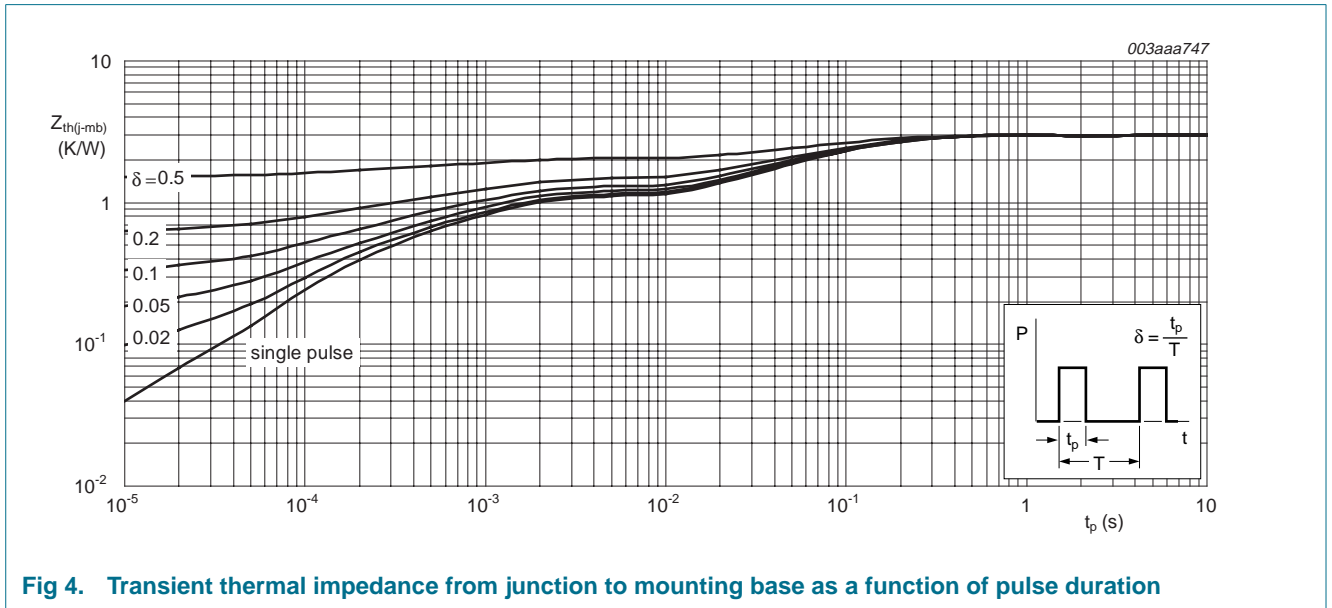


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

**Table 5: Characteristics**
*T<sub>j</sub> = 25 °C unless otherwise specified.*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V T <sub>j</sub> = 25 °C T <sub>j</sub> = -55 °C	30 27	- -	- -	V V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; <a href="#">Figure 9</a> and <a href="#">10</a> T <sub>j</sub> = 25 °C T <sub>j</sub> = 150 °C T <sub>j</sub> = -55 °C	1 0.6 -	1.5 - -	2 - 2.2	V V V
I <sub>DSS</sub>	drain-source leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V T <sub>j</sub> = 25 °C T <sub>j</sub> = 150 °C	- - -	- - -	1 100	μA μA
I <sub>GSS</sub>	gate-source leakage current	V <sub>GS</sub> = ±15 V; V <sub>DS</sub> = 0 V	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; <a href="#">Figure 6</a> and <a href="#">8</a> T <sub>j</sub> = 25 °C T <sub>j</sub> = 150 °C V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; <a href="#">Figure 6</a> and <a href="#">8</a>	- - -	14.1 24 18.8	16.9 28.7 23.5	mΩ mΩ mΩ
<b>Dynamic characteristics</b>						
Q <sub>g(tot)</sub>	total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 4.5 V; <a href="#">Figure 11</a> and <a href="#">12</a>	-	8.2	-	nC
Q <sub>gs</sub>	gate-source charge		-	2.3	-	nC
Q <sub>gs1</sub>	pre-V <sub>GS(th)</sub> gate-source charge		-	0.9	-	nC
Q <sub>gs2</sub>	post-V <sub>GS(th)</sub> gate-source charge		-	1.4	-	nC
Q <sub>gd</sub>	gate-drain (Miller) charge		-	2.9	-	nC
V <sub>plat</sub>	plateau voltage		-	2.6	-	V
Q <sub>g(tot)</sub>	total gate charge	I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 4.5 V	-	6.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 12 V; f = 1 MHz; <a href="#">Figure 14</a>	-	680	-	pF
C <sub>oss</sub>	output capacitance		-	280	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	135	-	pF
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 0 V; f = 1 MHz	-	1090	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; R <sub>L</sub> = 1 Ω; V <sub>GS</sub> = 4.5 V;	-	9	-	ns
t <sub>r</sub>	rise time	R <sub>G</sub> = 5.6 Ω	-	18	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	16	-	ns
t <sub>f</sub>	fall time		-	33	-	ns
<b>Source-drain diode</b>						
V <sub>SD</sub>	source-drain (diode forward) voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; <a href="#">Figure 13</a>	-	0.86	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 15 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V;	-	34	-	ns
Q <sub>r</sub>	recovered charge	V <sub>R</sub> = 30 V	-	12	-	nC

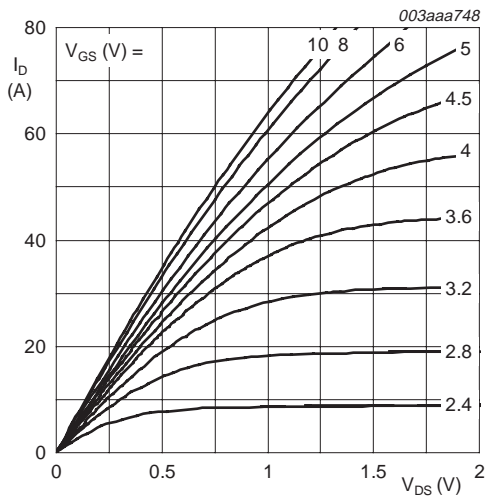


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

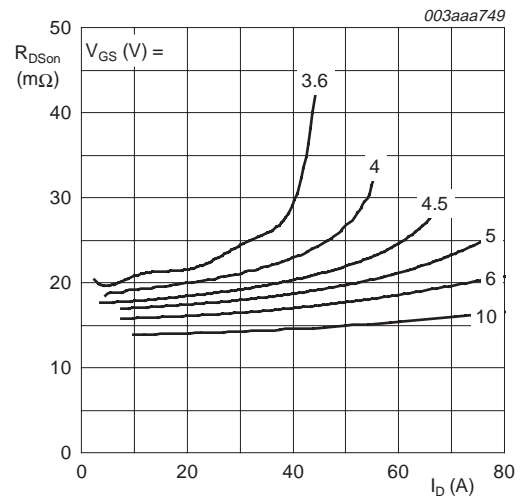


Fig 6. Drain-source on-state resistance as a function of drain current; typical values

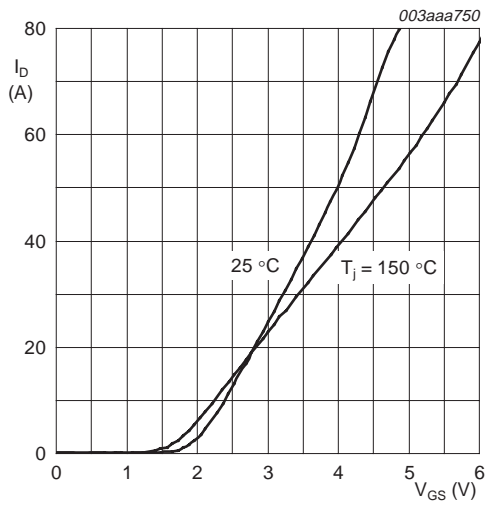


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

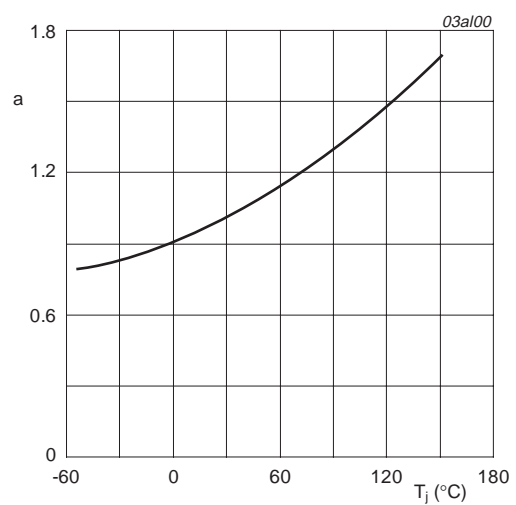
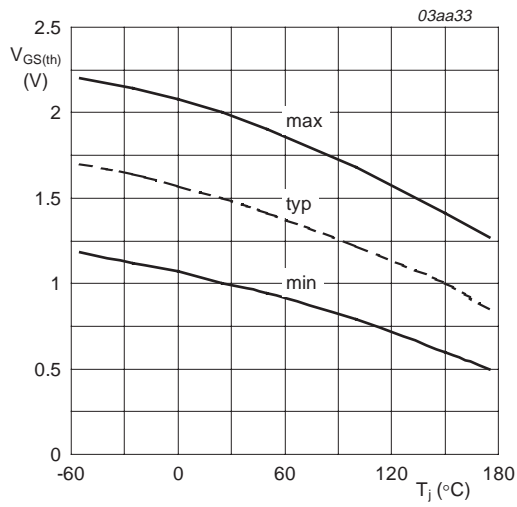
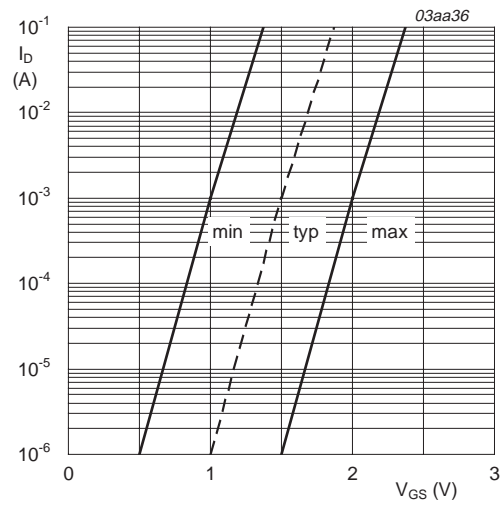


Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



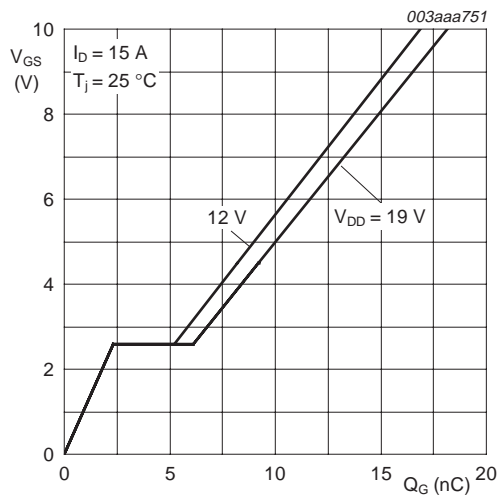
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



$T_j = 25 \text{ }^\circ\text{C}; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



$I_D = 15 \text{ A}; V_{DS} = 12 \text{ V and } 19 \text{ V}$

Fig 11. Gate-source voltage as a function of gate charge; typical values

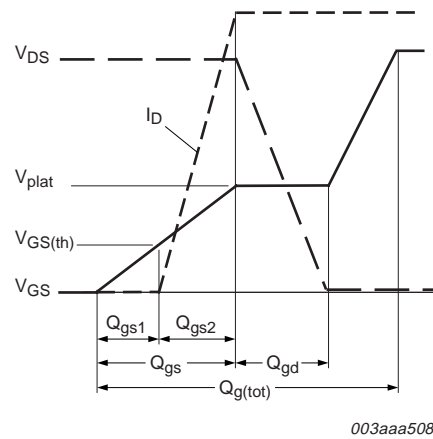
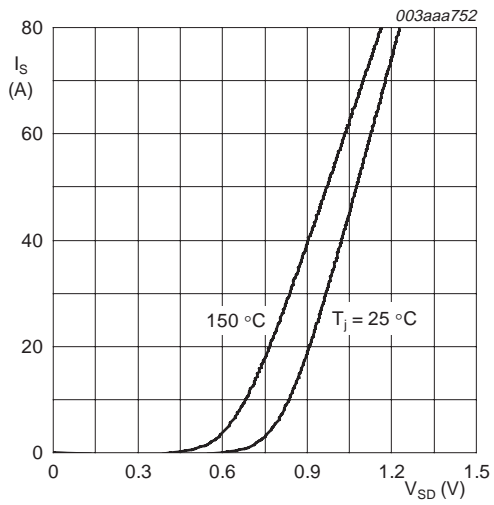
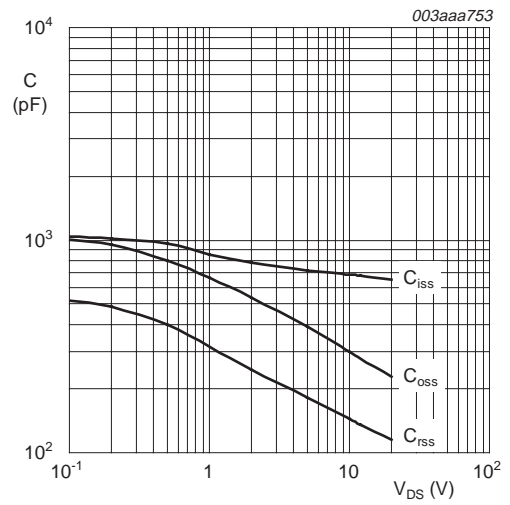


Fig 12. Gate charge waveform definitions



$T_j = 25^\circ\text{C}$  and  $150^\circ\text{C}$ ;  $V_{GS} = 0\text{ V}$

**Fig 13. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



$V_{GS} = 0\text{ V}$ ;  $f = 1\text{ MHz}$

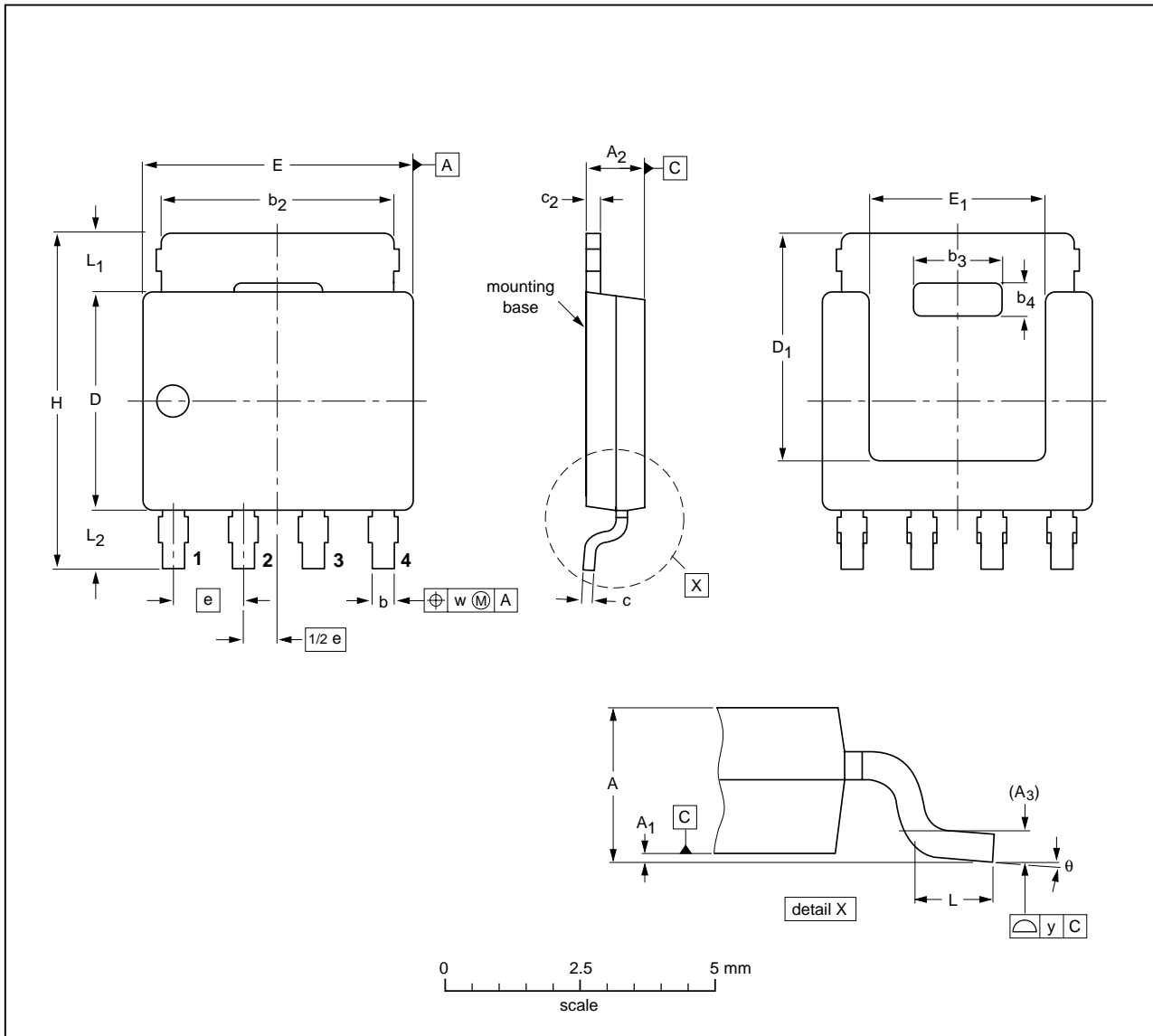
**Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



7. Package outline

Plastic single-ended surface mounted package (LPAK); 4 leads

SOT669



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b	b <sub>2</sub>	b <sub>3</sub>	b <sub>4</sub>	c	c <sub>2</sub>	D <sup>(1)</sup>	D <sub>1</sub> <sup>(1)</sup> max	E <sup>(1)</sup>	E <sub>1</sub> <sup>(1)</sup>	e	H	L	L <sub>1</sub>	L <sub>2</sub>	w	y	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT669		MO-235			03-09-15 04-10-13

Fig 15. Package outline SOT669 (LPAK)

## 8. Revision history

Table 6: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PH16030L_1	20050224	Product data sheet	-	9397 750 14431	-

## 9. Data sheet status

Level	Data sheet status <sup>[1]</sup>	Product status <sup>[2] [3]</sup>	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Date of release: 24 February 2005  
Document number: 9397 750 14431

Published in The Netherlands